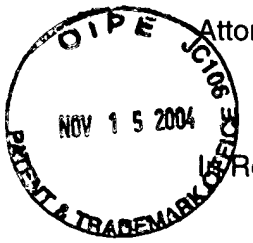
IFW



Attorney's Docket No.: 42P15685 PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Re Patent Application of:	)	
	)	
Scott A. Hareland et al.	)	Examiner: Unassigned
	)	
Application No.: 10/607,769	)	Art Unit: Unassigned
	)	
Filed: June 27, 2002	)	
	)	
For: NONPLANAR SEMICONDUCTOR DEVICE WITH PARTIALLY OR FULLY WRAPPED AROUND GATE ELECTRODE AND METHODS OF FABRICATION	)	

Commissioner for Patents
P.O. Box 1450
Alexandria, Virginia 22313-1450

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Sir:

Enclosed is a copy of Information Disclosure Citation Form PTO-1449 or PTO/SB/08 together with copies of the documents cited on that form, except for copies not required to be submitted (e.g., copies of U.S. patents and U.S. published patent applications need not be enclosed). It is respectfully requested that the cited documents be considered and that the enclosed copy of Information Disclosure Citation Form PTO-1449 or PTO/SB/08 be initialed by the Examiner to indicate such consideration and a copy thereof returned to applicant(s).

Pursuant to 37 C.F.R. § 1.97, the submission of this Information Disclosure Statement is not to be construed as a representation that a search

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Teresa Mattox
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(Signature of person mailing correspondence)

LJV/cak (10/27/04)

has been made and is not to be construed as an admission that the information cited in this statement is material to patentability.

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X ____ 37 C.F.R. §1.97(b).

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If there are any additional charges, please charge Deposit Account No. 02-2666.

Respectfully submitted,

BLAKELY, SOKOLOFF, TAYLOR & ZAFMAN LLP

Dated: 11/4, 2004

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Substitute for Form 1449/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Complete if Known	
Application Number	10/607,769
Filing Date	June 27, 2003
First Named Inventor:	Scott A. Hareland
Art Unit	Unknown
Examiner Name	Unknown
Attorney Docket Number	42P15685

Sheet	1	of	2

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	Document Number Number-Kind Code[2] (If known)		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		US-	6,716,684 B1	4/6/2004	Krivokapic et al.	
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		US-				
		US-				

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	Foreign Patent Document Country Code[3] Number[4] Kind Code[5] (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T[6]
		EP 0 623 963 A1	11/9/1994	Siemens AG		
		WO 02/43151A	5/30/2002	Hitachi ULSI Sys Co Ltd		

Examiner Signature		Date Considered	

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT *(use as many sheets as necessary)*				Application Number	10/607,769
				Filing Date	June 27, 2002
				First Named Inventor:	Scott A. Hareland et al.
				Art Unit	Unknown
				Examiner Name	Unknown
Sheet	2	of	2	Attorney Docket Number	42P15685

NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T[2]
		V. Subramanian et al., " A Bulk-Si-Compatible Ultrathin-body SOI Technology for Sub-100m MOSFETS" Proceeding of the 57th Annual Device Research Conference, pp. 28-29 (1999)	
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		International Search Report PCT/US 03/26242	
		International Search Report PCT/US 03/39727	
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